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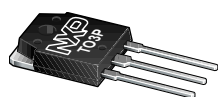
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# BYV415K-600P

Dual ultrafast power diode

24 December 2014

Product data sheet

## 1. General description

Dual ultrafast power diode in a SOT1259 (3-lead TO-3P) plastic package.

## 2. Features and benefits

- Very low on-state loss
- Fast switching
- Low leakage current
- Low thermal resistance

## 3. Applications

- Active PFC in air conditioner
- Interleaved PFC topology in switched-mode power supplies

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	-	600	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$ ; $T_{mb} \leq 126\text{ }^{\circ}\text{C}$ ; square-wave pulse; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	15	A
<b>Static characteristics</b>						
$V_F$	forward voltage	$I_F = 15\text{ A}$ ; $T_j = 150\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 6</a>	-	1.1	1.4	V
<b>Dynamic characteristics</b>						
$t_{rr}$	reverse recovery time	$I_F = 1\text{ A}$ ; $V_R = 30\text{ V}$ ; $dI_F/dt = 100\text{ A}/\mu\text{s}$ ; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>	-	25	50	ns



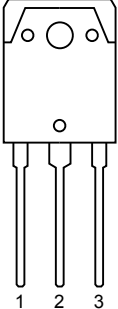
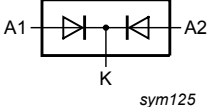
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Dual ultrafast power diode

**5. Pinning information**

**Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	 <p><b>TO3P (SOT1259)</b></p>	
2	K	cathode		
3	A2	anode 2		
mb	mb	mounting base; connected to cathode		

**6. Ordering information**

**Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
BYV415K-600P	TO3P	Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO3P	SOT1259

**7. Marking**

**Table 4. Marking codes**

Type number	Marking code
BYV415K-600P	BYV415K-600P

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**BYV415K-600P**

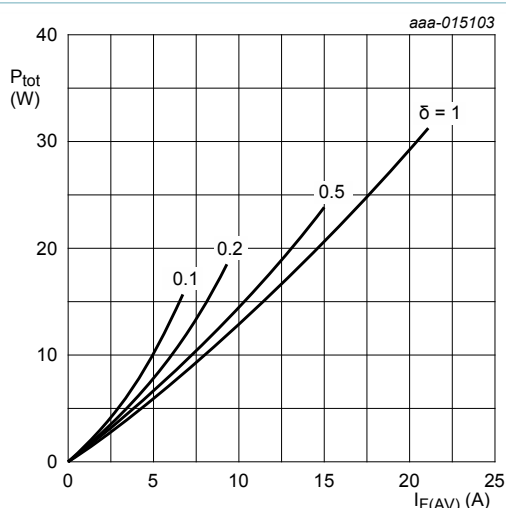
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**8. Limiting values**

**Table 5. Limiting values**

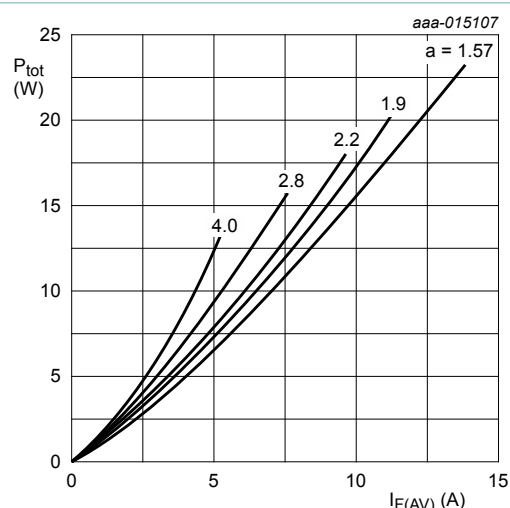
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	600	V
$V_{RWM}$	crest working reverse voltage		-	600	V
$V_R$	reverse voltage	DC	-	600	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$ ; $T_{mb} \leq 126\text{ }^\circ\text{C}$ ; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	15	A
$I_{O(AV)}$	average output current	$\delta = 0.5$ ; $T_{mb} \leq 126\text{ }^\circ\text{C}$ ; square-wave pulse; both diodes conducting	-	30	A
$I_{FRM}$	repetitive peak forward current	$\delta = 0.5$ ; $t_p = 25\text{ }\mu\text{s}$ ; $T_{mb} \leq 126\text{ }^\circ\text{C}$ ; Square-wave pulse	-	15	A
$I_{FSM}$	non-repetitive peak forward current	$t_p = 10\text{ ms}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; sine-wave pulse; per diode; Fig. 4	-	140	A
		$t_p = 8.3\text{ ms}$ ; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; sine-wave pulse; per diode; Fig. 4	-	155	A
$T_{stg}$	storage temperature		-65	175	$^\circ\text{C}$
$T_j$	junction temperature		-	175	$^\circ\text{C}$



$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$   
 $V_o = 1.135\text{ V}$ ;  $R_s = 0.017\text{ }\Omega$

**Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values**



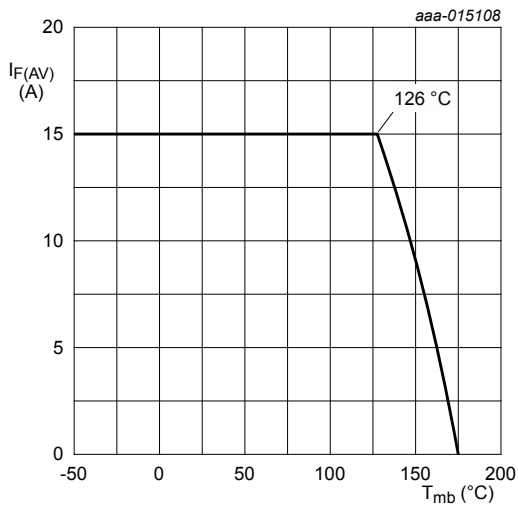
$a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$   
 $V_o = 1.135\text{ V}$ ;  $R_s = 0.017\text{ }\Omega$

**Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values**

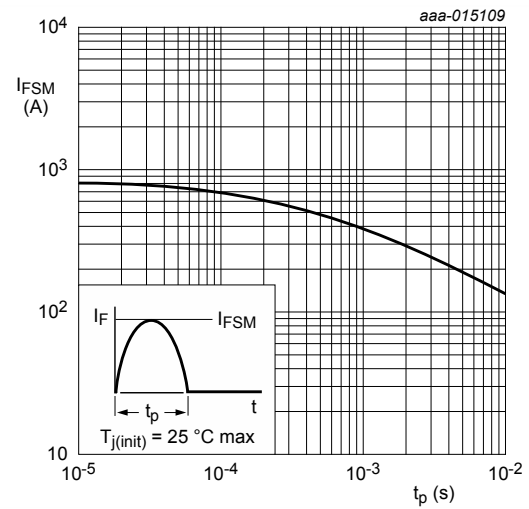
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**Dual ultrafast power diode**



**Fig. 3. Forward current as a function of mounting base temperature; maximum values**

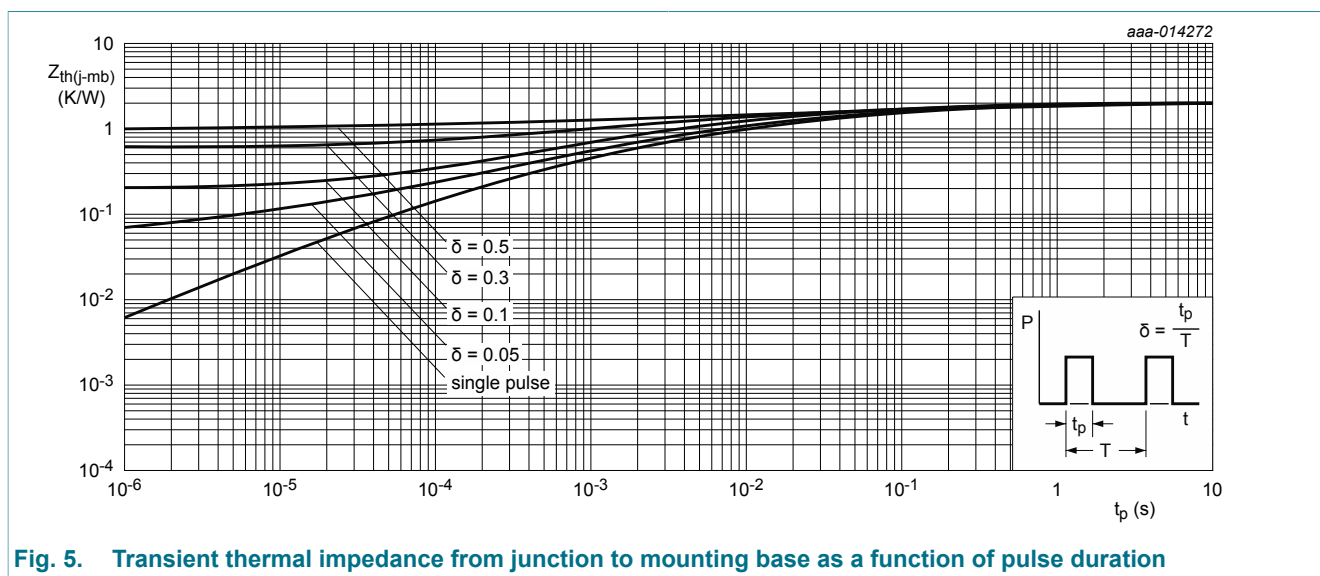


**Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values**

**9. Thermal characteristics**

**Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	with heatsink compound; per diode; <a href="#">Fig. 5</a>	-	1.2	2	K/W
		with heatsink compound; both diodes conducting	-	0.65	1.2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	45	-	K/W



**Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration**

## 10. Characteristics

**Table 7. Characteristics**

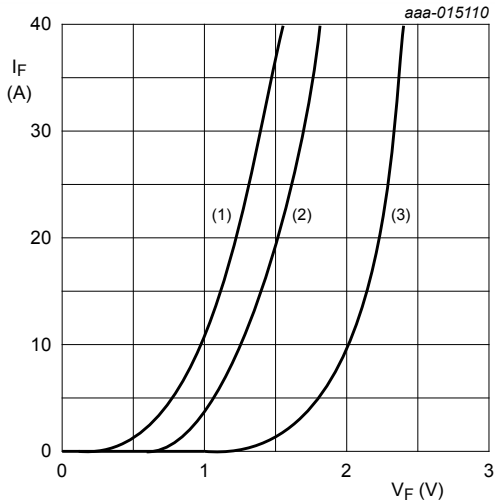
characteristics are per diode unless otherwise stated

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_F$	forward voltage	$I_F = 15\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 6</a>	-	1.4	2.1	V
		$I_F = 15\text{ A}$ ; $T_j = 150\text{ °C}$ ; <a href="#">Fig. 6</a>	-	1.1	1.4	V
$I_R$	reverse current	$V_R = 600\text{ V}$ ; $T_j = 25\text{ °C}$	-	-	10	$\mu\text{A}$
		$V_R = 600\text{ V}$ ; $T_j = 150\text{ °C}$	-	-	500	$\mu\text{A}$
<b>Dynamic characteristics</b>						
$Q_r$	recovered charge	$I_F = 15\text{ A}$ ; $V_R = 400\text{ V}$ ; $di_F/dt = 200\text{ A}/\mu\text{s}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	125	-	nC
		$I_F = 15\text{ A}$ ; $V_R = 400\text{ V}$ ; $di_F/dt = 200\text{ A}/\mu\text{s}$ ; $T_j = 125\text{ °C}$ ; <a href="#">Fig. 7</a>	-	318	-	nC
$t_{rr}$	reverse recovery time	$I_F = 1\text{ A}$ ; $V_R = 30\text{ V}$ ; $di_F/dt = 100\text{ A}/\mu\text{s}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	25	50	ns
		$I_F = 15\text{ A}$ ; $V_R = 400\text{ V}$ ; $di_F/dt = 200\text{ A}/\mu\text{s}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	45	-	ns
		$I_F = 15\text{ A}$ ; $V_R = 400\text{ V}$ ; $di_F/dt = 200\text{ A}/\mu\text{s}$ ; $T_j = 125\text{ °C}$ ; <a href="#">Fig. 7</a>	-	65	-	ns
		$I_F = 15\text{ A}$ ; $V_R = 400\text{ V}$ ; $di_F/dt = 500\text{ A}/\mu\text{s}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	34	-	ns
$I_{RM}$	peak reverse recovery current	$I_F = 15\text{ A}$ ; $V_R = 400\text{ V}$ ; $di_F/dt = 200\text{ A}/\mu\text{s}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	5.5	-	A
		$I_F = 15\text{ A}$ ; $V_R = 400\text{ V}$ ; $di_F/dt = 200\text{ A}/\mu\text{s}$ ; $T_j = 125\text{ °C}$ ; <a href="#">Fig. 7</a>	-	9.7	-	A

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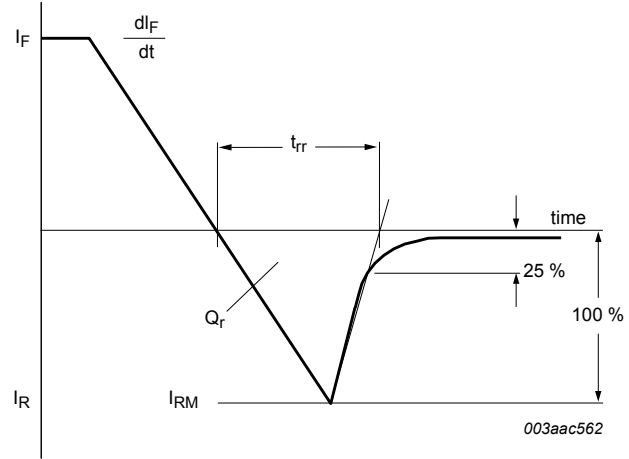
Dual ultrafast power diode



$V_o = 1.135 \text{ V}; R_s = 0.017 \Omega$

- (1)  $T_j = 150 \text{ }^\circ\text{C}$ ; typical values
- (2)  $T_j = 150 \text{ }^\circ\text{C}$ ; maximum values
- (3)  $T_j = 25 \text{ }^\circ\text{C}$ ; maximum values

**Fig. 6. Forward current as a function of forward voltage**



**Fig. 7. Reverse recovery definitions; ramp recovery**



11. Package outline

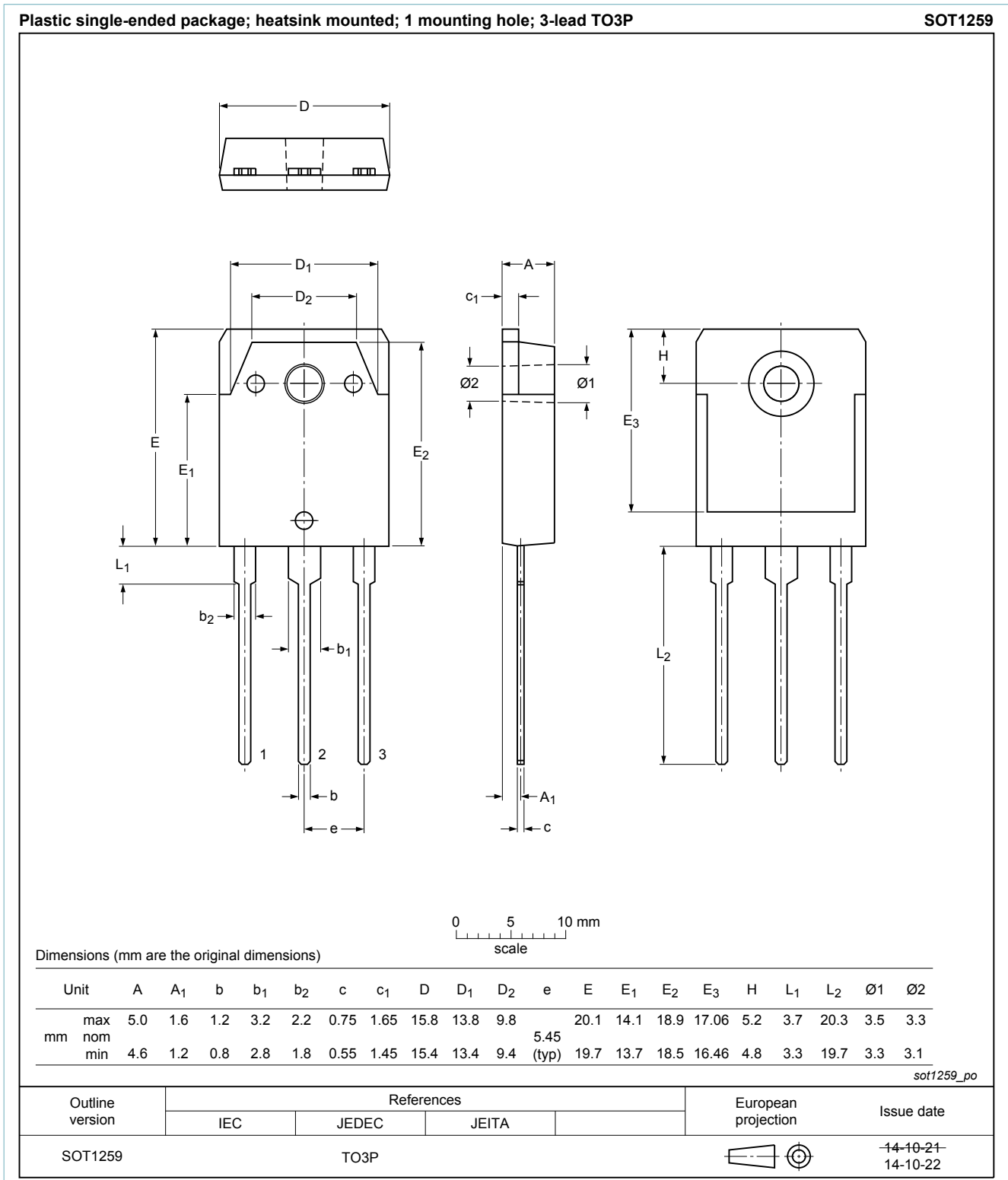


Fig. 8. Package outline TO3P (SOT1259)

## 12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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